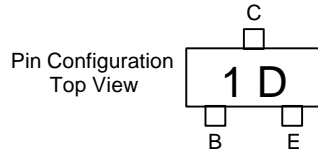


MMBTA42

Features

- Surface Mount SOT-23 Package
- Capable of 300mWatts of Power Dissipation



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emmitter Breakdown Voltage* ($I_C=1.0mA$, $I_B=0$)	300		Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=100\mu A$, $I_E=0$)	300		Vdc
$V_{(BR)EBO}$	Emmitter-Base Breakdown Voltage ($I_E=100\mu A$, $I_C=0$)	6.0		Vdc
I_{CBO}	Collector Cutoff Current ($V_{CB}=200V$, $I_E=0$)		0.1	μA
I_{EBO}	Emmitter Cutoff Current ($V_{EB}=6.0V$, $I_C=0$)		0.1	μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain* ($I_C=1.0mA$, $V_{CE}=10V$) ($I_C=10mA$, $V_{CE}=10V$) ($I_C=30mA$, $V_{CE}=10V$)	25 40 40	----	
$V_{CE(sat)}$	Collector-Emmitter Saturation Voltage ($I_C=20mA$, $I_B=2.0mA$)		0.5	Vdc
$V_{BE(sat)}$	Base-Emmitter Saturation Voltage ($I_C=20mA$, $I_B=2.0mA$)		0.9	Vdc

SMALL-SIGNAL CHARACTERISTICS

f_T	Current Gain-Bandwidth Product ($I_C=10mA$, $V_{CE}=20V$, $f=100MHz$)	50		MHz
C_{cb}	Collector-Emmitter Capacitance ($V_{CB}=20V$, $I_E=0$, $f=1.0MHz$)		3.0	pF

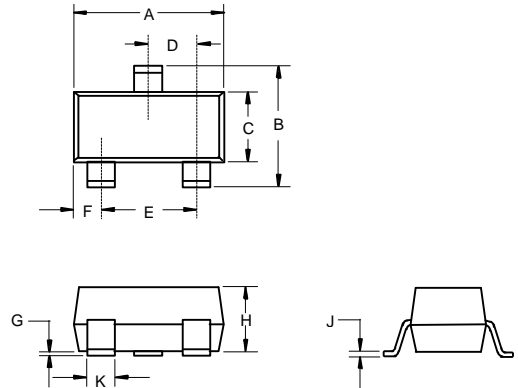
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, ⁽¹⁾ $T_A = 25^\circ C$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, ⁽²⁾ $T_A = 25^\circ C$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	°C

*Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2.0\%$

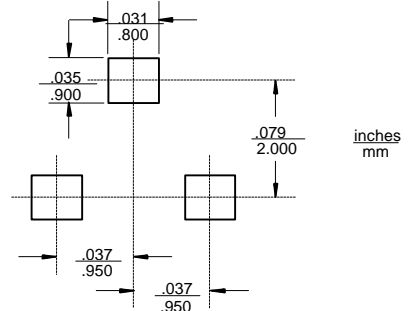
NPN Silicon High Voltage Transistor

SOT-23



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.110	.120	2.80	3.04	
B	.083	.098	2.10	2.64	
C	.047	.055	1.20	1.40	
D	.035	.041	.89	1.03	
E	.070	.081	1.78	2.05	
F	.018	.024	.45	.60	
G	.0005	.0039	.013	.100	
H	.035	.044	.89	1.12	
J	.003	.007	.085	.180	
K	.015	.020	.37	.51	

Suggested Solder Pad Layout



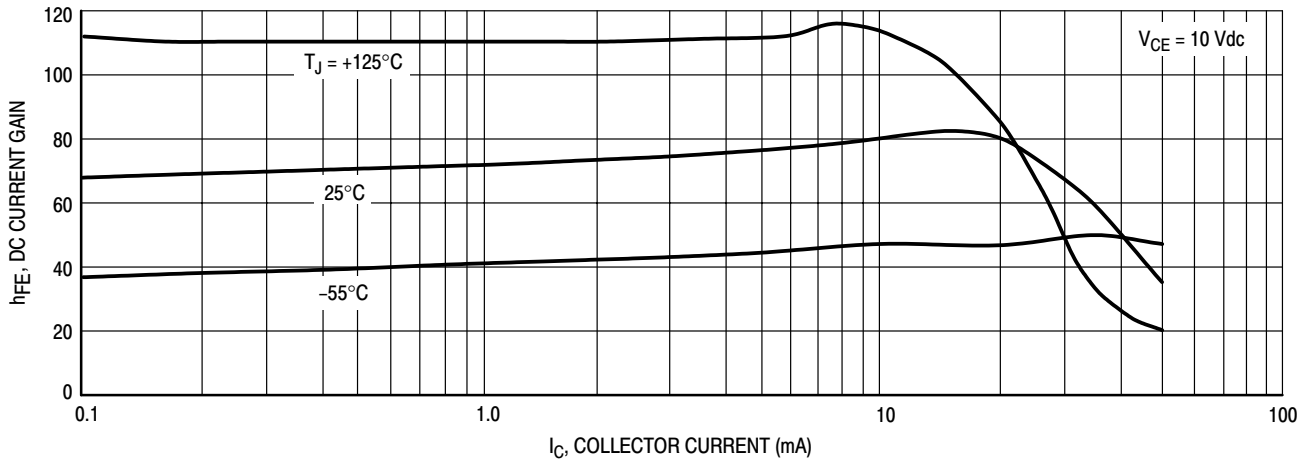


Figure 1. DC Current Gain

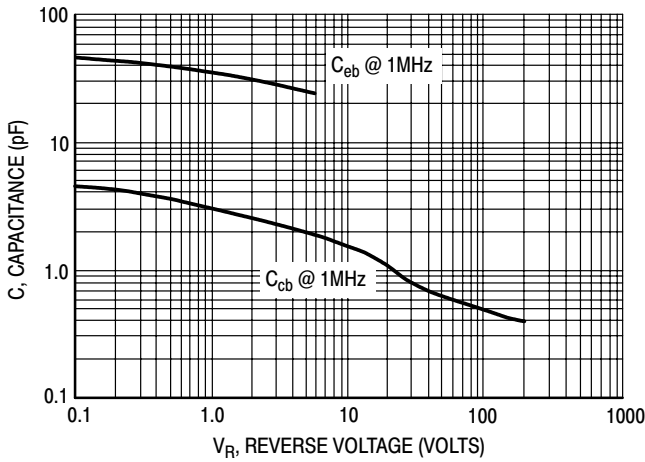


Figure 2. Capacitance

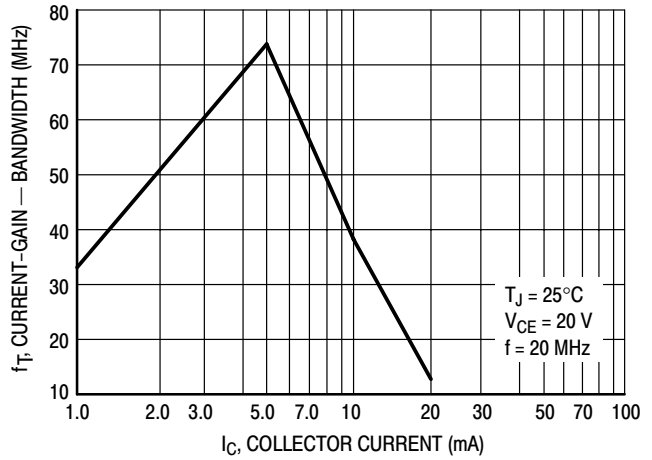


Figure 3. Current-Gain - Bandwidth

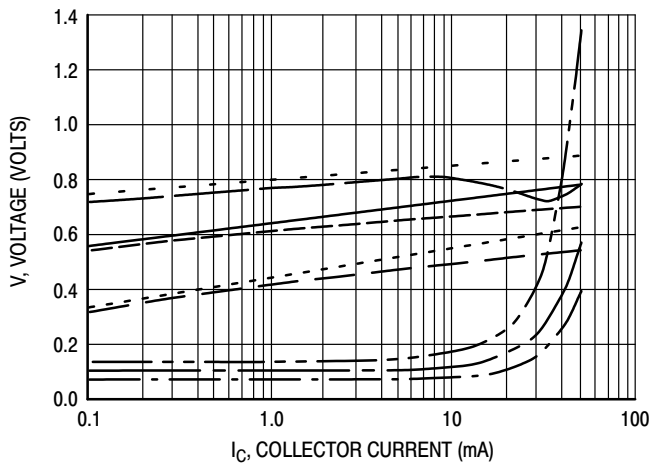


Figure 4. "ON" Voltages

- $V_{CE(sat)}$ @ 25°C, $I_C/I_B = 10$
- $V_{CE(sat)}$ @ 125°C, $I_C/I_B = 10$
- $V_{CE(sat)}$ @ -55°C, $I_C/I_B = 10$
- $V_{BE(sat)}$ @ 25°C, $I_C/I_B = 10$
- $V_{BE(sat)}$ @ 125°C, $I_C/I_B = 10$
- $V_{BE(sat)}$ @ -55°C, $I_C/I_B = 10$
- $V_{BE(on)}$ @ 25°C, $V_{CE} = 10$ V
- $V_{BE(on)}$ @ 125°C, $V_{CE} = 10$ V
- $V_{BE(on)}$ @ -55°C, $V_{CE} = 10$ V